

Product Summary

V _{SSS}	R _{SS(on)} TYP	I _S
12V	4.8mΩ@4.5V	9A
	5.1mΩ@3.8V	
	5.6mΩ@3.1V	
	6.6mΩ@2.5V	

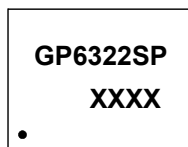
Feature

- Trench Technology
- Common-drain design
- Supper high density cell design
- ESD Diode-Protected Gate
- CSP

Application

- Lithium-ion Battery Charging and Discharging Switch

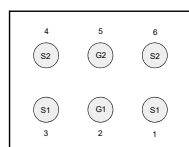
MARKING:



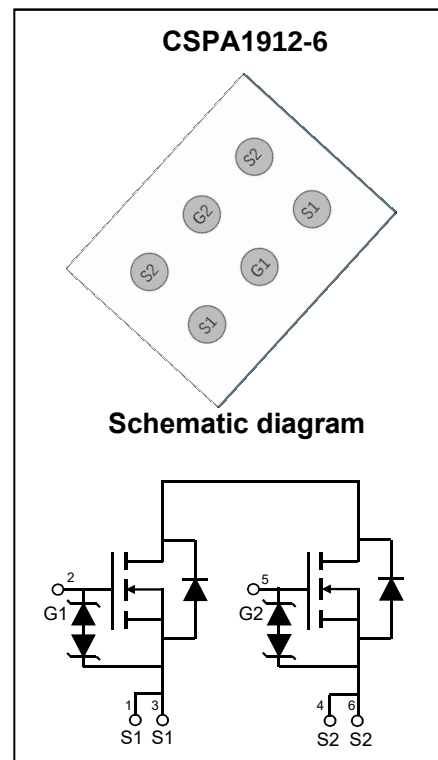
Top View



Left-right turn



Bottom View



GP6322SP = Device Code

Source1:1,3

Gate1:2

XXXX = Date Code

Source2:4,6

Gate2:5

Solid Dot = Pin 1

ABSOLUTE MAXIMUM RATINGS (T_A = 25°C unless otherwise noted)

Parameter		Symbol	Value	Unit
Source-Source Voltage		V _{SSS}	12	V
Gate-Source Voltage		V _{GS}	±10	V
Source Current	DC ¹	I _S	9	A
	Pulse ²	I _{SP}	90	A
Total Power Dissipation		P _D	2.1	W
Channel Temperature		T _{CH}	150	°C
Storage Temperature		T _{STG}	-55~ +150	°C

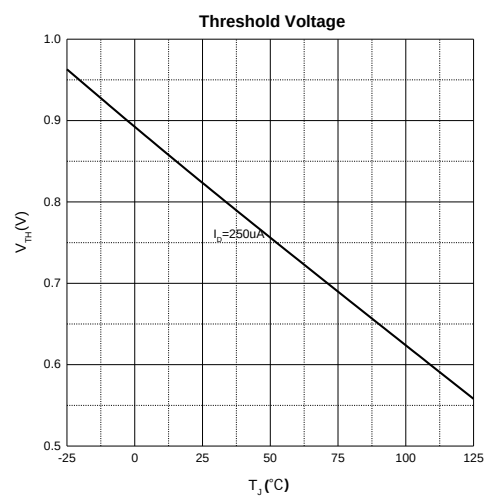
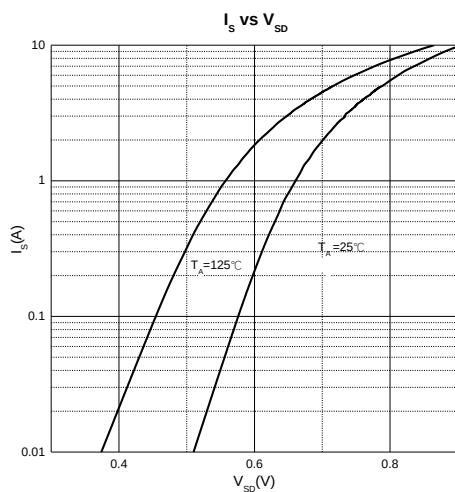
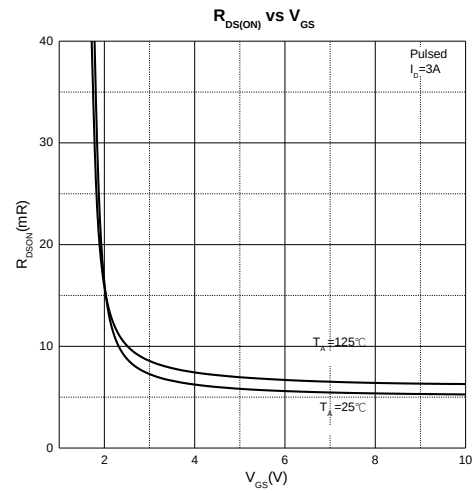
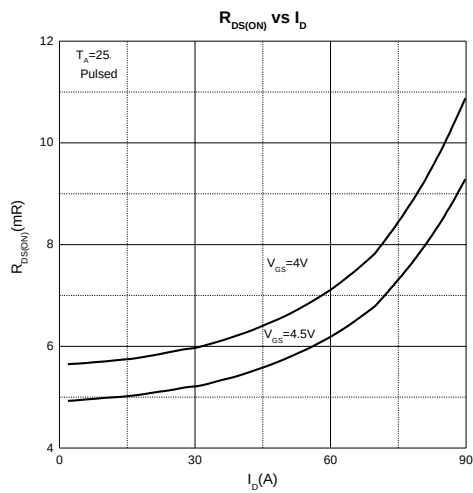
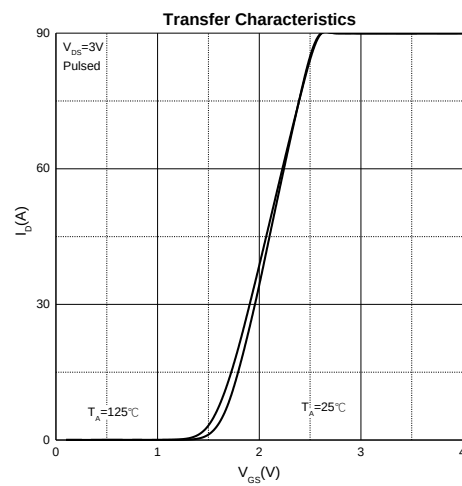
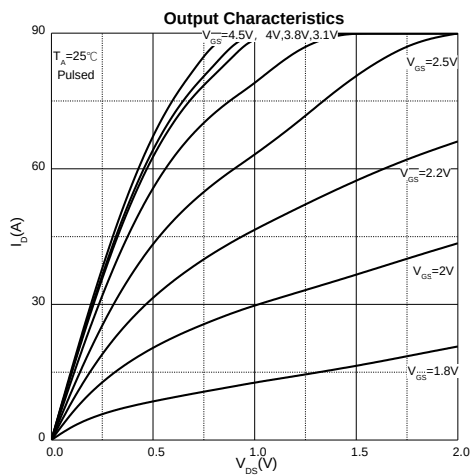
MOSFET ELECTRICAL CHARACTERISTICS ($T_A = 25^\circ\text{C}$ unless otherwise noted)

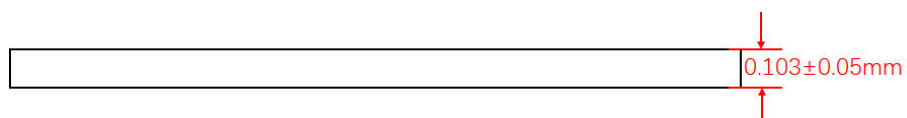
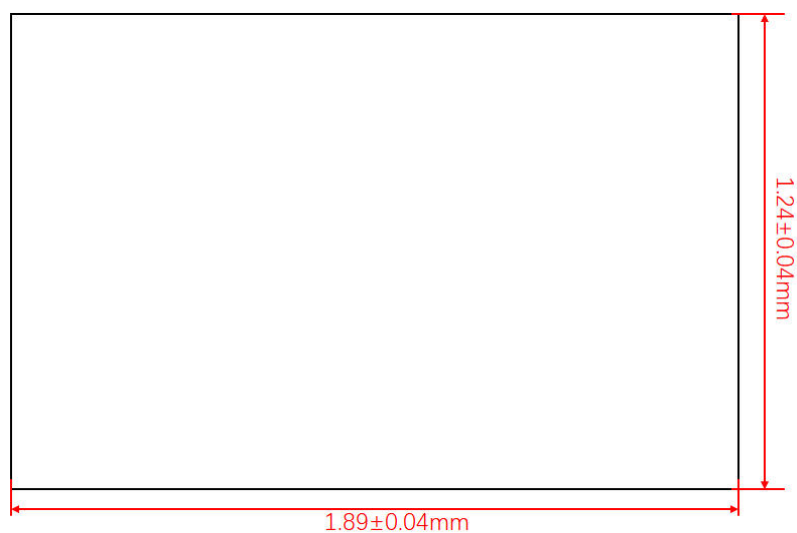
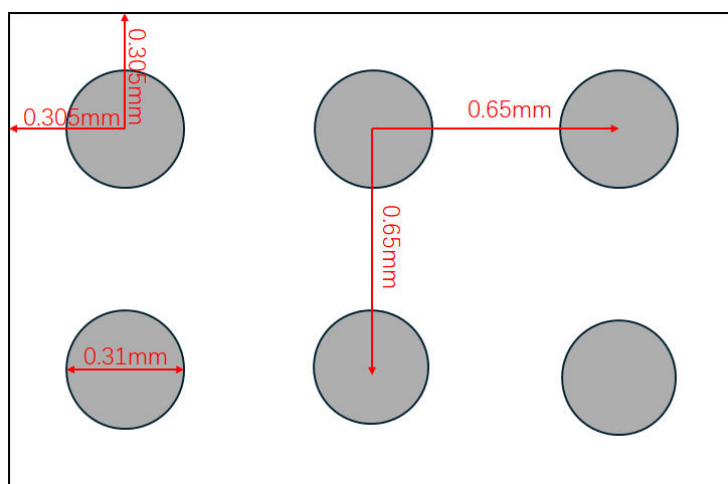
Parameter	Symbol	Test Condition	Min	Type	Max	Unit
Off Characteristics						
Source-Source Breakdown Voltage	BV _{SSS}	V _{GS} = 0V , I _S = 250μA	12			V
Zero Gate Voltage Source Current	I _{SSS}	V _{SS} = 12V, V _{GS} = 0V			1	μA
Gate-Source Leakage Current	I _{GSS}	V _{GS} = ±10V, V _{SS} = 0V			±10	μA
On Characteristics						
Gate-Source Threshold Voltage	V _{GS(th)}	V _{SS} =10V, I _S = 1mA	0.4	0.9	1.4	V
Source-Source On-resistance	R _{SS(on)}	V _{GS} = 4.5V, I _S =3A	3.0	4.8	5.4	mΩ
		V _{GS} = 3.8V, I _S =3A	3.3	5.1	6.0	
		V _{GS} = 3.1V, I _S =3A	3.5	5.6	7.7	
		V _{GS} = 2.5V, I _S =3A	4.5	6.6	13.6	
Dynamic Characteristics ³						
Input Capacitance	C _{iss}	V _{SS} = 6V, V _{GS} = 0V, f = 0.1MHz		1435		pF
Output Capacitance	C _{oss}			455		
Reverse Transfer Capacitance	C _{rss}			332		
Switching Characteristics ³						
Total Gate Charge	Q _g	V _{SS} = 10V, V _{GS} = 6V, I _S = 10A		39		nC
Gate-Source Charge	Q _{gs}			3.6		
Gate-Drain Charge	Q _{gd}			8.8		
Turn-on Delay Time	t _{d(on)}	V _{DD} = 6V, V _{GS} = 4V,R _L =1.3Ω		270		ns
Turn-on Rise Time	t _r			340		
Turn-off Delay Time	t _{d(off)}			1350		
Turn-off Fall Time	t _f			1250		
Source-Drain Diode Characteristics						
Diode Forward Voltage	V _{F(S-S)}	V _{GS} = 0V, I _S = 2A			1.2	V

Notes :

1. Mounted on FR-4 board (25.4 mm × 25.4 mm × t1.0 mm) with 1oz. Copper, using the minimum recommended pad size.
2. Pulse Test : Pulse Width = 10 μs , duty cycle $\leq 1\%$.
3. Guaranteed by design, not subject to production testing.

Typical Characteristics



CSPA1912-6 Package Information


Attention:

- GreenPower Electronics reserves the right to improve product design function and reliability without notice.
- Any and all semiconductor products have certain probability to fail or malfunction, which may result in personal injury, death or property damage. Customer are solely responsible for providing adequate safe measures when design their systems.
- GreenPower Electronics products belong to consumer electronics or other civilian electronic products.